Elektronische Bauelemente

SCS202NF

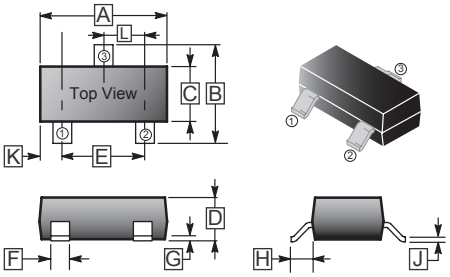
80 V, 300 mA
Plastic-Encapsulated, Dual Series Chips
Small Signal Switching Diode

RoHS Compliant Product
A suffix of "-C" specifies halogen and lead free

FEATURES

- Ultra high speed switching
- High reliability
- Suitable for high packaging density layout
- Fast reverse recovery time : t_{rr} = 1.5ns (typ.)
- Construction: silicon epitaxial planar

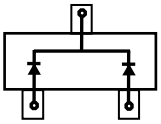
SOT-323



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.00	2.20	F	0.20	0.40
B	2.15	2.45	G	-	-
C	1.15	1.35	H	0.525 REF.	
D	0.90	1.10	J	0.08	0.15
E	1.20	1.40			

PACKAGING INFORMATION

- Four types of packaging are available
- Weight: 0.0078 g (Approx.)



MARKING CODE

N , **A3**

ABSOLUTE MAXIMUM RATINGS (each diode)

Parameter	Symbol	Ratings	Unit
Peak Reverse Voltage	V_{RM}	80	V
DC Reverse Voltage	V_R	80	V
Maximum (Peak) Forward Current	I_{FM}	300	mA
Average Forward Current	I_O	100	mA
Surge Current 1μS	I_{SURGE}	4	A
Total Power Dissipation	P_D	200	mW
Junction, Storage Temperature	T_J, T_{STG}	+150, -55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (at Ta = 25°C unless otherwise specified)(each diode)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward Voltage	V_F	-	-	1.2	V	I_F = 100 mA
Reverse Voltage Leakage Current	I_R	-	-	0.1	μA	V_R = 70V
Diode Capacitance	C_T	-	-	3.5	pF	V_R = 6 V, f = 1 MHz
Reverse Recovery Time	T_{RR}	-	-	4.0	nS	V_R = 6 V, I_F = 5 mA

Notes: 1. FR–5 = 1.0 X 0.75 X 0.062 in.
2. Alumina = 0.4 X 0.3 X 0.024 in. 99.5% alumina.

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CHARACTERISTIC CURVES

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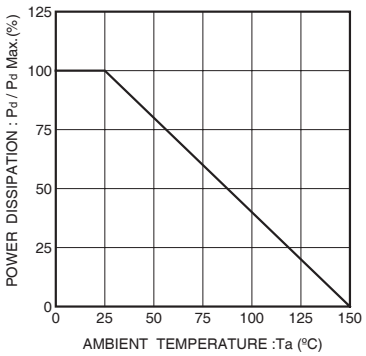


Fig.1 Power attenuation curve

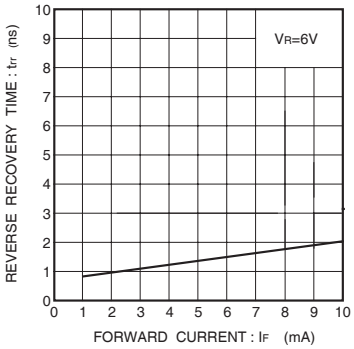


Fig.2 Reverse recovery time

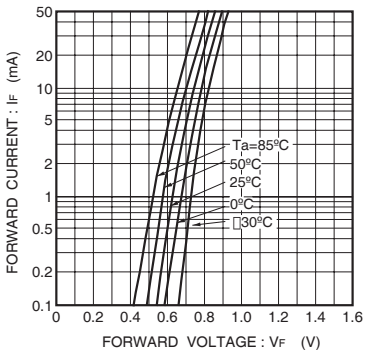


Fig.3 Forward characteristics

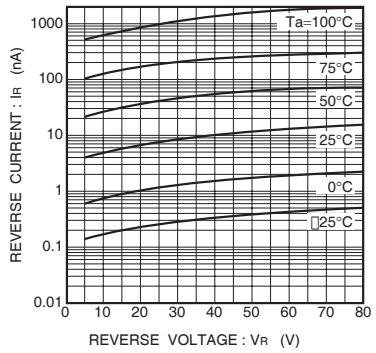


Fig.4 Reverse characteristics

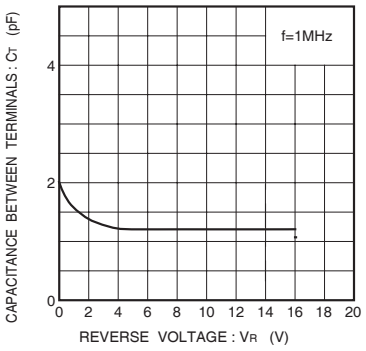


Fig.5 Capacitance between terminals characteristics

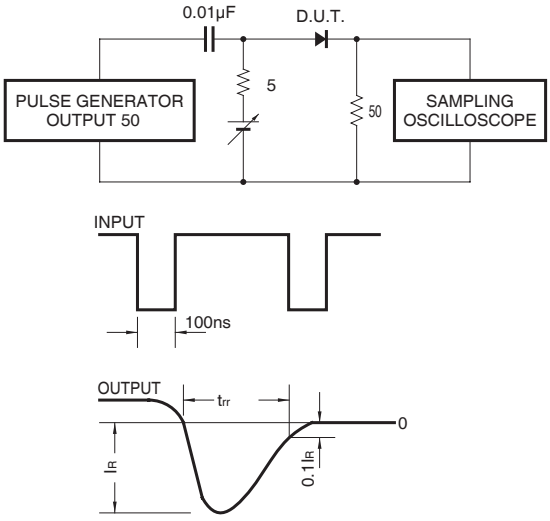


Fig.6 Reverse recovery time (t_{rr}) measurement circuit